1N5061 THRU 1N5062

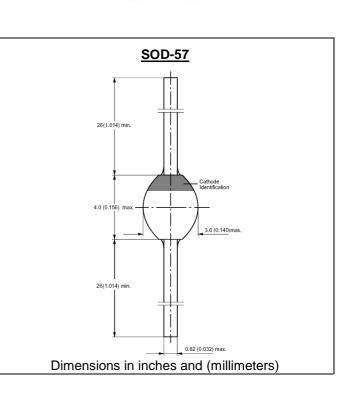
SINTERED GLASS JUNCTION AVALANCHE RECTIFIER

VOLTAGE: 600V to 800V

CURRENT: 2.0A

FEATURE

Glass passivated High maximum operating temperature Low leakage current Excellent stability Guaranteed avalanche energy absorption capability



MECHANICAL DATA

Case: SOD-57 sintered glass case Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C Polarity: color band denotes cathode end Mounting position: any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

		SYMBOL	1N5061	1N5062	units
Maximum Recurrent Peak Reverse Voltage		V _{RRM}	600	800	V
Maximum RMS Voltage		V _{RMS}	420	560	V
Maximum DC blocking Voltage		V _{DC}	600	800	V
Maximum Average Forward Rectified Current 3/8"lead length at Ttp =45°C		I _{FAV}	2.0		А
Peak Forward Surge Current at t=10ms half sinewave		I _{FSM}	50		A
Maximum Forward Voltage at rated Forward Current at 1.0A		V _F	1.0		V
Maximum DC Reverse Current at rated DC blocking voltage	Ta =25°C Ta =165°C	I _R		1.0 150.0	
Typical Reverse Recovery Time (Note 1)		Trr	3000		nS
Diode capacitance at0V,1MHz		Cd		50	pF
Typical Thermal Resistance	(Note 2)	R _{th(ja)}	1	00	K/W
Storage and Operating Junction Temperation	Tstg, Tj	-65 to +175		O°	

Note:

1. Reverse Recovery Condition If =0.5A, Ir =1.0A, Irr =0.25A

2. Device mounted on epoxy-glass printed-circuit board, 1.5mm thick

RATINGS AND CHARACTERISTIC CURVES 1N5061 THRU 1N5062

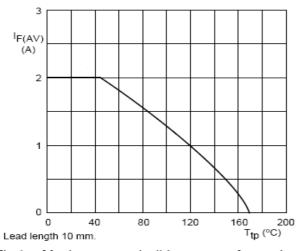


Fig.1 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

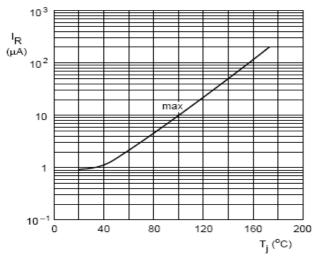
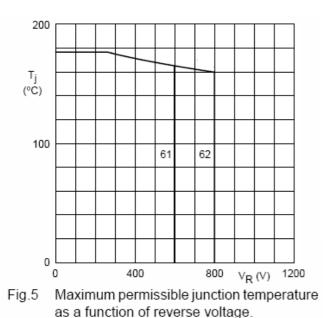


Fig.3 Reverse current as a function of junction temperature; maximum values.



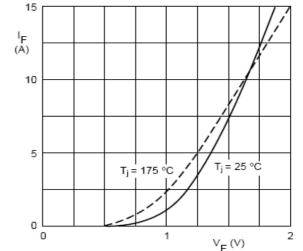


Fig.2 Forward current as a function of forward voltage; maximum values.

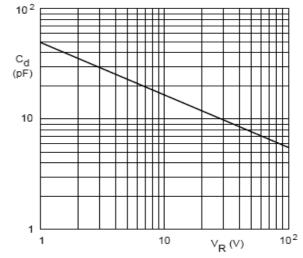


Fig.4 Diode capacitance as a function of reverse voltage; typical values.